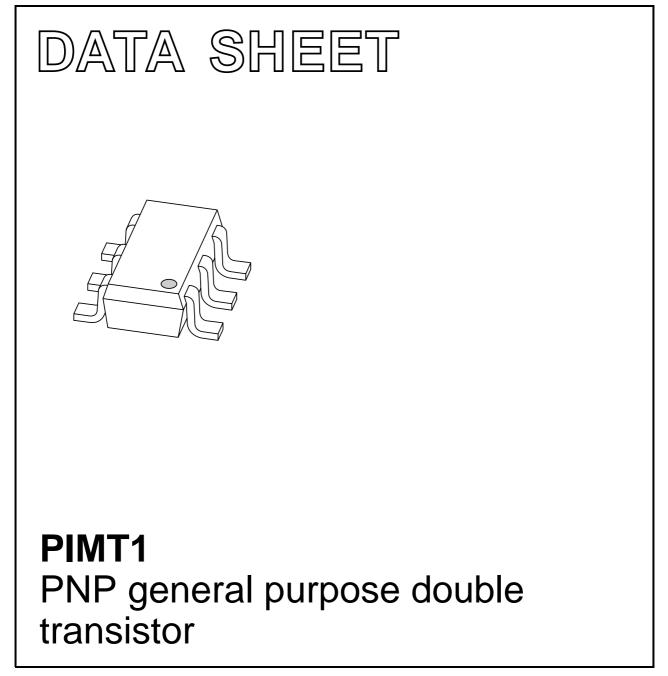
DISCRETE SEMICONDUCTORS



Product data sheet

2001 Oct 22



PNP general purpose double transistor

FEATURES

- 600 mW total power dissipation
- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and required PCB area
- Reduced pick and place costs.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP transistor pair in an SC-74 (SOT457) plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PIMT1	M1		

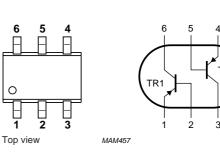


Fig.1 Simplified outline (SC74; SOT457) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor	·		·	·
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	—	-40	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM} peak base current			-	-200	mA
P _{tot} total power dissipation		$T_{amb} \le 25 \text{ °C}; \text{ note } 1$	-	300	mW
T _{stg} storage temperature			-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	9	·	·		·
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	600	mW

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	

PIMT1

PNP general purpose double transistor

PIMT1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	208	K/W

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transi	stor				
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-100	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 \text{ °C}$	-	-10	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 V; I_C = 0$	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -6 \text{ V}; \text{ I}_{C} = -1 \text{ mA}$	120	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -50$ mA; $I_{\rm B} = -5$ mA; note 1	-	-200	mV
Cc	collector capacitance	$V_{CB} = -12 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	2.2	pF
f _T	transition frequency	$V_{CE} = -12 \text{ V}; \text{ I}_{C} = -2 \text{ mA};$ f = 100 MHz	100	-	MHz

Note

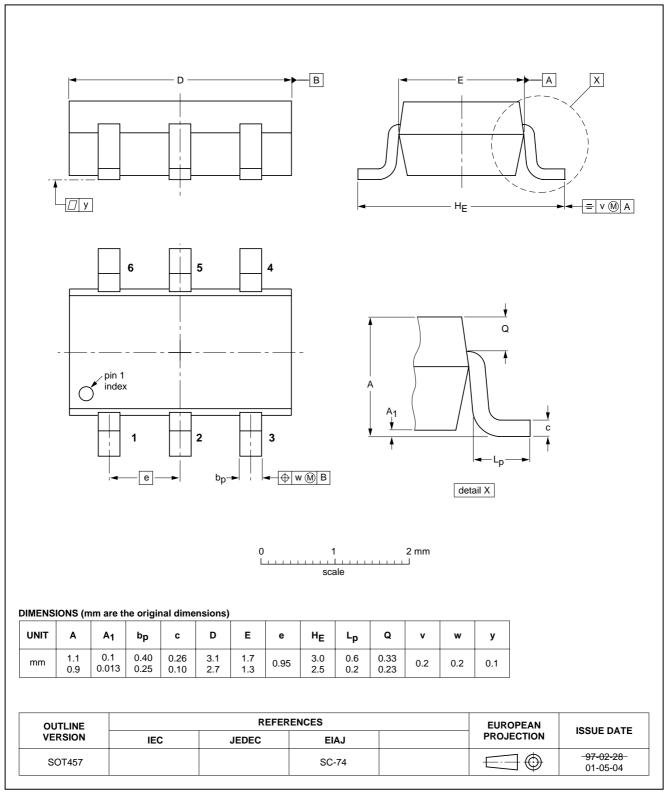
1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

PIMT1

PNP general purpose double transistor

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads



SOT457

PNP general purpose double transistor

PIMT1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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